

IN THE CLAIMS:

Please cancel claim 2. Please also amend claims 1 and 3, and add new claims 4-6, as shown in the complete list of claims that is presented below.

1. (currently amended) An ONO flash memory array for ~~improving a~~ reducing disturbance between adjacent memory cells, comprising:

a substrate having a first and second buried diffusion regions;

a channel between the first and second buried diffusion regions;

an ONO layer above the channel for memory storage;

a first pocket of a first concentration implanted on one side of the channel close to the first buried diffusion region; and

a second pocket of a second concentration implanted on the other side of the channel close to the second buried diffusion region, wherein the first concentration is higher than the second concentration.

Claim 2 (cancelled).

3. (currently amended) An ONO flash memory array for ~~improving a~~ reducing disturbance between first and second adjacent memory cells, comprising:

a substrate having a first and second buried diffusion regions, the second buried diffusion region having a first portion in the first memory cell and a second portion in the second memory cell;

a channel in the first memory between the first ~~and second~~ buried diffusion regions; region and the first portion of the second buried diffusion region.
an ONO layer above the channel for memory storage in the first memory cell; ~~and~~
a ~~pocket~~ first implanted ~~on one side of the channel close to~~ pocket at the first
portion of the second buried diffusion ~~region.~~ region, the first pocket
having a first concentration; and
a second implanted pocket at the second portion of the second diffusion region,
the second pocket having a second concentration that is different from the
first concentration.

4. (new) An ONO flash memory array for reducing disturbance between first and second adjacent memory cells, comprising:

a substrate having first and second buried diffusion regions, the second buried diffusion region having a first portion in the first memory cell and a second portion in the second memory cell;
a channel in the first memory cell between the first buried diffusion region and the first portion of the second buried diffusion region;
an ONO layer above the channel for memory storage in the first memory cell; and
means for providing the second buried diffusion region with an implanted pocket arrangement that is asymmetrical with respect to the first and second portions thereof.

5. (new) The memory array of claim 4, wherein the means comprises an implanted pocket at one of the portions of the second buried diffusion region, the other portion lacking a pocket.

6. (new) The memory array of claim 4, wherein the means comprises a first implanted pocket at the first portion of the second buried diffusion region and a second implanted pocket at the second portion, the first and second implanted pockets having different concentrations.

IN THE DRAWINGS:

Approval of the proposed change that is marked in red ink on the copy of Figure 3 attached to this Amendment is respectfully requested.